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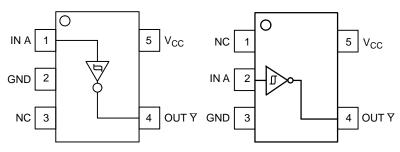
Schmitt Inverter

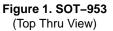
The NL17SG14 MiniGate[™] is an advanced high–speed CMOS Schmitt Inverter in ultra–small footprint.

The NL17SG14 input structure provides protection when voltages up to 4.6 V are applied.

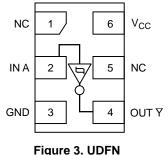
Features

- Wide Operating V_{CC} Range: 0.9 V to 3.6 V
- High Speed: $t_{PD} = 3.7$ ns (Typ) at $V_{CC} = 3.0$ V, $C_L = 15$ pF
- Low Power Dissipation: $I_{CC} = 0.5 \ \mu A$ (Max) at $T_A = 25^{\circ}C$
- 4.6 V Overvoltage Tolerant (OVT) Input Pins
- Ultra-Small Packages
- NLV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC–Q100 Qualified and PPAP Capable
- These Devices are Pb–Free, Halogen Free/BFR Free and are RoHS Compliant









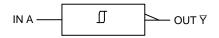


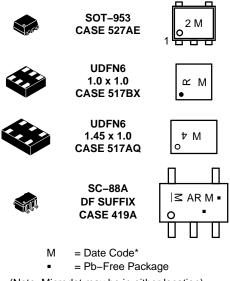
Figure 4. Logic Symbol



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MARKING DIAGRAMS



(Note: Microdot may be in either location) *Date Code orientation and/or position may vary depending upon manufacturing location.

PIN ASSIGNMENT					
	SOT-953	UDFN6			
1	IN A	NC	NC		
2	GND	IN A	IN A		
3	NC	GND	GND		
4	Ουτ γ	OUT Y	OUT 7		
5	V _{CC}	V _{CC}	NC		
6			V _{CC}		

FUNCTION TABLE

A Input	Y Output
L	Н
Н	L

ORDERING INFORMATION

See detailed ordering and shipping information on page 5 of this data sheet.

MAXIMUM RATINGS

Symbol	Paramete	Parameter		Unit	
V _{CC}	DC Supply Voltage		–0.5 to +5.5	V	
V _{IN}	DC Input Voltage		-0.5 to +4.6	V	
V _{OUT}	DC Output Voltage	Output at High or Low State Power–Down Mode ($V_{CC} = 0 V$)	-0.5 to V _{CC} + 0.5 -0.5 to +4.6	V	
I _{IK}	DC Input Diode Current	V _{IN} < GND	-20	mA	
Ι _{ΟΚ}	DC Output Diode Current	V _{OUT} < GND	-20	mA	
I _{OUT}	DC Output Source/Sink Current		±20	mA	
I _{CC}	DC Supply Current per Supply Pin	±20	mA		
I _{GND}	DC Ground Current per Ground Pin		±20	mA	
T _{STG}	Storage Temperature Range		-65 to +150	°C	
ΤL	Lead Temperature, 1 mm from Case for 10 Sec	conds	260	°C	
TJ	Junction Temperature Under Bias		+150	°C	
MSL	Moisture Sensitivity		Level 1		
F _R	Flammability Rating Oxygen Index: 28 to 34		UL 94 V–0 @ 0.125 in		
V_{ESD}	ESD Withstand Voltage	Human Body Model (Note 2) Machine Model (Note 3)	>2000 >100	V	
ILATCHUP	Latchup Performance Above	V_{CC} and Below GND at 125°C (Note 4)	±100	mA	

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality Should not be assumed, damage may occur and reliability may be affected.
 Measured with minimum pad spacing on an FR4 board, using 10 mm-by-1 inch, 2-ounce copper trace with no air flow.
 Tested to EIA/JESD22-A114-A.
 Tested to EIA/JESD22-A115-A.

4. Tested to EIA/JESD78.

RECOMMENDED OPERATING CONDITIONS

Symbol	Characteristics	Min	Max	Unit
V _{CC}	Positive DC Supply Voltage	0.9	3.6	V
V _{IN}	Digital Input Voltage	0.0	3.6	V
V _{OUT}	Output Voltage Output at High or Low State Power–Down Mode (V _{CC} = 0 V)	0.0 0.0	V _{CC} 3.6	V
T _A	Operating Temperature Range	-55	+125	°C
$\Delta t / \Delta V$	Input Transition Rise or Fail Rate	0	No Limit	ns/V

Functional operation above the stresses listed in the Recommended Operating Ranges is not implied. Extended exposure to stresses beyond the Recommended Operating Ranges limits may affect device reliability.

DC ELECTRICAL CHARACTERISTICS

				V _{cc}		T _A = 25°C		–55°C ≤ 1	_A ≤ 125°C	
Symbol	Parameter	c	Condition	(V)	Min	Тур	Max	Min	Max	Unit
V_{T+}	V _{T+} Positive–Going			0.9	0.64	0.7	0.86	0.62	0.87	
Input Threshold Voltage				1.1	0.73	0.81	0.95	0.71	1	
				1.4	0.86	0.94	1.16	0.84	1.2	
				1.65	0.95	1.06	1.25	0.94	1.3	V
				2.3	1.22	1.36	1.6	1.18	1.65	
				3.0	1.51	1.8	2.05	1.38	2.1	
V _{T-}	Negative-			0.9	0.09	0.23	0.30	0.08	0.33	
	Going Input Threshold			1.1	0.15	0.33	0.39	0.12	0.43	
	Voltage			1.4	0.3	0.47	0.54	0.25	0.55	
				1.65	0.35	0.6	0.65	0.3	0.65	V
				2.3	0.55	0.85	0.88	0.5	0.88	
				3.0	0.95	1.13	1.16	0.9	1.16	
V _H	Hysteresis			0.9	0.15	0.5	0.75	0.2	0.8	
	Voltage			1.1	0.15	0.5	0.75	0.2	0.8	
				1.4	0.15	0.5	0.75	0.2	0.8	
				1.65	0.15	0.5	0.75	0.2	0.8	V
				2.3	0.15	0.5	0.75	0.2	0.8	
				3.0	0.25	0.65	0.85	0.3	0.9	
V _{OH}	High–Level	V _{IN} =	I _{OH} = -20 μA	0.9	0.75			0.75		V
	Output Voltage	V _{IH} or V _{IL}	I _{OH} = -0.3 mA	1.1 to 1.3	0.75 x V _{CC}			0.75 x V _{CC}		
			I _{OH} = -1.7 mA	1.4 to 1.6	0.75 x V _{CC}			0.75 x V _{CC}		
			I _{OH} = -3.0 mA	1.65 to 1.95	V _{CC} – 0.45			V _{CC} – 0.45		
			$I_{OH} = -4.0 \text{ mA}$	2.3 to 2.7	2.0			2.0		
			I _{OH} = -8.0 mA	3.0 to 3.6	2.48			2.48		
V _{OL}	Low–Level Output Voltage	V _{IN} = V _{IH} or	I _{OL} = 20 μA	0.9			0.1		0.1	V
	Output voltage	VIL	I _{OL} = 0.3 mA	1.1 to 1.3			0.25 x V _{CC}		0.25 x V _{CC}	
			I _{OL} = 1.7 mA	1.4 to 1.6			0.25xV CC		0.25 x V _{CC}	
			I _{OL} = 3.0 mA	1.65 to 1.95			0.45		0.45	
			l _{OL} = 4.0 mA	2.3 to 2.7			0.4		0.4	
			l _{OL} = 8.0 mA	3.0 to 3.6			0.4		0.4	
I _{IN}	Input Leakage Current	$0 \le V_{IN} \le 3.6 V$		0 to 3.6			±0.1		±1.0	μA
I _{CC}	Quiescent Supply Current	V _{IN} =	V _{CC} or GND	3.6			0.5		10.0	μA

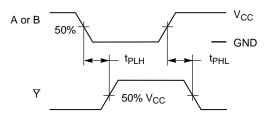
Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

					T _A = 25 °C	;		_ = ⊳ +125°C	
Symbol	Parameter	Test Condition	V _{CC} (V)	Min	Тур	Max	Min	Max	Unit
t _{PLH} ,	Propagation Delay, A or Y	$C_{L} = 10 \text{ pF},$	0.9	-	27.3	-	-	-	ns
t _{PHL}	AOIY	$R_L = 1 M\Omega$	1.1 to 1.3	-	13.0	22.6	1.0	35.9	
			1.4 to 1.6	-	7.5	10.5	1.0	11.3	
			1.65 to 1.95	-	6.0	7.8	1.0	8.2	
			2.3 to 2.7	-	4.3	5.4	1.0	5.8	
			3.0 to 3.6	-	3.5	4.4	1.0	4.6	
		$C_{L} = 15 pF,$	0.9	-	29.5	-	-	-	ns
		$R_L = 1 M\Omega$	1.1 to 1.3	-	14.3	25.1	1.0	41.6	
			1.4 to 1.6	-	8.0	11.5	1.0	12.6	
			1.65 to 1.95	-	6.3	8.4	1.0	8.7	
			2.3 to 2.7	-	4.6	5.7	1.0	6.1	
			3.0 to 3.6	-	3.7	4.6	1.0	5.0	
		$C_L = 30 \text{ pF},$ $R_L = 1 \text{ M}\Omega$	0.9	-	40.5	-	-	-	ns
		$R_{L} = 1 \text{ IVIS2}$	1.1 to 1.3	-	19.6	35.7	1.0	58.1	
			1.4 to 1.6	-	10.7	15.8	1.0	17.6	
			1.65 to 1.95	-	7.8	10.7	1.0	11.7	
			2.3 to 2.7	-	5.4	6.9	1.0	8.1	
			3.0 to 3.6	-	4.3	5.2	1.0	6.1	
C _{IN}	Input Capacitance		0 to 3.6		3	-	_	_	pF
C _O	Output Capacitance	V _O = GND	0		3	_	_	_	pF
C _{PD}	Power Dissipation Capacitance (Note 5)	f = 10 MHz	0.9 to 3.6	-	4	-	_	_	pF

AC ELECTRICAL CHARACTERISTICS (Input t_r = t_f = 3.0 ns)

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.
5. C_{PD} is defined as the value of the internal equivalent capacitance which is calculated from the dynamic operating current consumption without load. Average operating current can be obtained by the equation: I_{CC(OPR)} = C_{PD} • V_{CC} • f_{in} + I_{CC}. C_{PD} is used to determine the no–load dynamic power consumption; P_D = C_{PD} • V_{CC}² • f_{in} + I_{CC} • V_{CC}.

NL17SG14





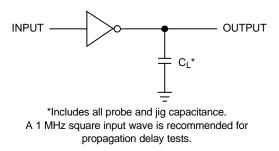


Figure 6. Test Circuit

ORDERING INFORMATION

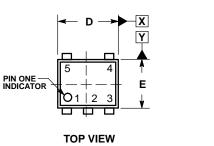
Device	Package	Shipping [†]
NL17SG14P5T5G	SOT–953 (Pb–Free)	8000 / Tape & Reel
NL17SG14DFT2G	SC–88A (Pb–Free)	3000 / Tape & Reel
NLV17SG14DFT2G*	SC–88A (Pb–Free)	3000 / Tape & Reel
NL17SG14AMUTCG (In Development)	UDFN6 1.45x1 mm (Pb-Free)	3000 / Tape & Reel
NL17SG14CMUTCG (In Development)	UDFN6 1x1 mm (Pb-Free)	3000 / Tape & Reel

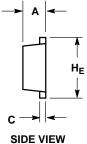
†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

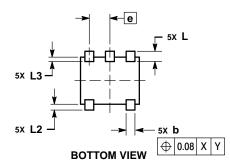
*NLV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC–Q100 Qualified and PPAP Capable.

PACKAGE DIMENSIONS

SOT-953 CASE 527AE ISSUE E



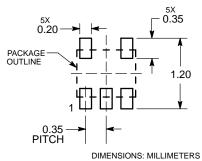




NOTES:
 1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
 2. CONTROLLING DIMENSION: MILLIMETERS
 3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF THE BASE MATERIAL.
 4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

FLASH, PROTRUSIONS, OR G					
	MILLIMETERS				
DIM	MIN	NOM	MAX		
Α	0.34	0.37	0.40		
b	0.10	0.15	0.20		
С	0.07	0.12	0.17		
D	0.95	1.00	1.05		
E	0.75	0.80	0.85		
е		0.35 BS	С		
HE	0.95	1.00	1.05		
L	0.175 REF				
L2	0.05	0.10	0.15		
L3			0.15		

SOLDERING FOOTPRINT*

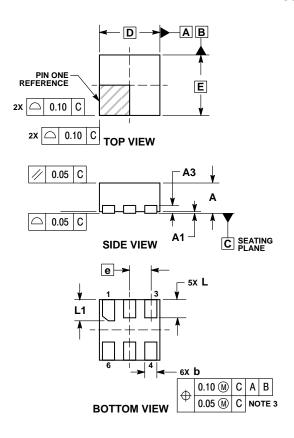


*For additional information on our Pb–Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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PACKAGE DIMENSIONS

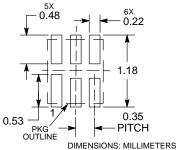
UDFN6 1.0x1.0, 0.35P CASE 517BX ISSUE O



- NOTES:
 DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
 CONTROLLING DIMENSION: MILLIMETERS.
 DIMENSION & APPLIES TO PLATED TERMINAL AND IS MEASURED BETWEEN 0.15 AND 0.20 MM FROM TERMINAL TIP.
 PACKAGE DIMENSIONS EXCLUSIVE OF BURRS AND MOLD FLASH.

BURRS AND MOLD FL				
	MILLIN	MILLIMETERS		
DIM	MIN MAX			
Α	0.45	0.55		
A1	0.00 0.05			
A3	0.13 REF			
b	0.12 0.22			
D	1.00	BSC		
Е	1.00	BSC		
е	0.35	BSC		
L	0.25 0.35			
L1	0.30	0.40		

RECOMMENDED **SOLDERING FOOTPRINT***



*For additional information on our Pb–Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

NL17SG14

PACKAGE DIMENSIONS

UDFN6 1.45x1.0, 0.5P CASE 517AQ ISSUE O

